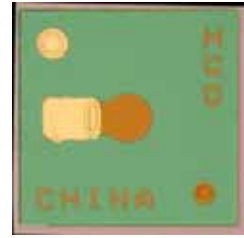


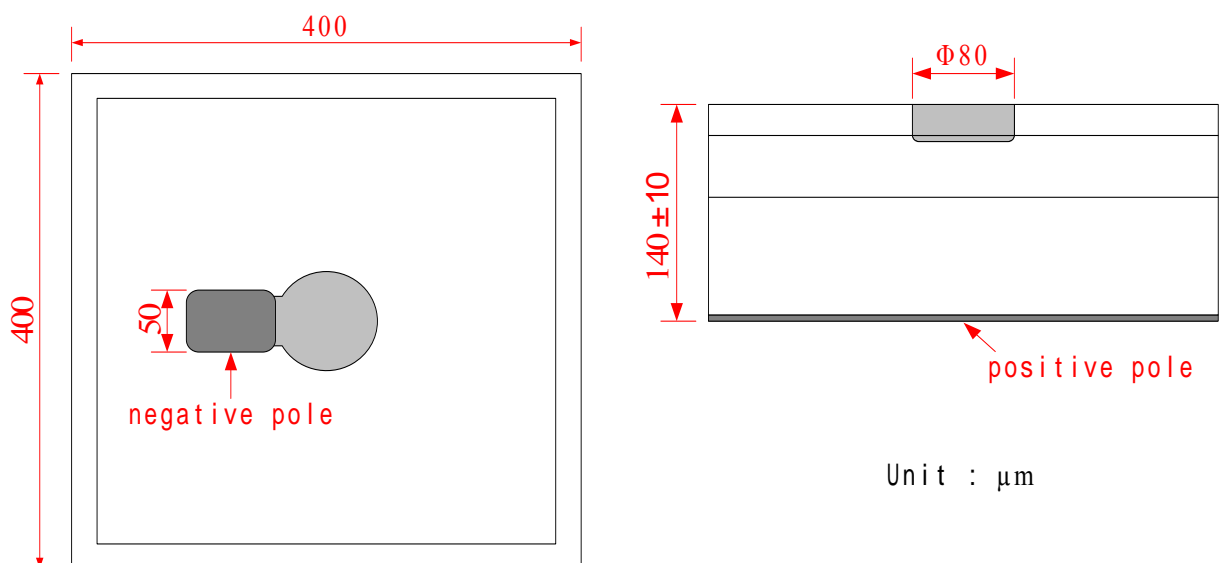
**Planar InGaAs/InP  $\Phi 80\mu\text{m}$  PIN Photodiode**
**CPD-P08**
**Features:**

- Low Dark Current Small Capacitance .
- High responsivity in the wavelength region of 1.00 $\mu\text{m}$  to 1.65 $\mu\text{m}$ .
- Planar Structure, Top illuminated.
- The CPD-P08 is designed for high speed data telecom application to 155Mbps, 622Mbps


**Specifications : Ambient Temperature=25**

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Dark Current	$I_d$	$V_R=5V$	-	—	0.5	nA
Capacitance	$C_p$	$V_R=5V$ F=1MHz	-	—	0.7	pF
Responsivity	R	$V_R=5V@1310\text{nm}$	0.85	0.90	-	A/W
Reverse Breakdown Voltage	$V_B$	1 $\mu\text{A}$	30	-	-	V
Saturation Power	$P_{\text{sat}}$	$V_R=5V@1550\text{nm}$	10	—	-	mW

**Avoid ESD; the device may be permanently damaged.**

**Chip Layout :**


**Statement:**

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